

# FJN3303 High Voltage Fast-Switching NPN Power Transistor

- High Voltage Capability
- · High Switching Speed
- · Suitable for Electronic Ballast and Charger



# Absolute Maximum Ratings $T_C = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	700	V
V <sub>CEO</sub>	Collector-Emitter Voltage	400	V
V <sub>EBO</sub>	Emitter-Base Voltage	9	V
I <sub>C</sub>	Collector Current (DC)	1.5	A
I <sub>CP</sub>	Collector Current (Pulse) *	3	Α
I <sub>B</sub>	Base Current (DC)	0.75	Α
I <sub>BP</sub>	Base Current (Pulse) *	1.5	A
P <sub>C</sub>	Collector Power Dissipation (T <sub>C</sub> = 25°C)	1.1	W
TJ	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	-65 ~ 150	°C

<sup>\*</sup> Pulse Test: Pulse Width = 5ms, Duty Cycle  $\leq 10\%$ 

# **Electrical Characteristics** $T_C = 25$ °C unless otherwise noted

Symbol	Parameter	Conditions	Min.	Тур.	Max	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	$I_C = 500\mu A, I_E = 0$	700			V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 5mA, I <sub>B</sub> = 0	400			V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 500μA, I <sub>C</sub> = 0	9			V
I <sub>CBO</sub>	Collector Cut-off Current	V <sub>CB</sub> = 700V, I <sub>E</sub> = 0			10	μΑ
I <sub>EBO</sub>	Emitter Cut-off Current	V <sub>EB</sub> = 9V, I <sub>C</sub> = 0			10	μΑ
h <sub>FE1</sub> h <sub>FE2</sub>	DC Current Gain	$V_{CE} = 2V, I_{C} = 0.5A$ $V_{CE} = 2V, I_{C} = 1.0A$	14 5		23	
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	$I_C = 0.5A, I_B = 0.1A$ $I_C = 1.0A, I_B = 0.25A$ $I_C = 1.5A, I_B = 0.5A$			0.5 1.0 3.0	V V V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	$I_C = 0.5A, I_B = 0.1A$ $I_C = 1.0A, I_B = 0.25A$			1.0 1.2	V V
f <sub>T</sub>	Current Gain Bandwidth Product	V <sub>CE</sub> = 10V, I <sub>C</sub> = 0.1A	4			MHz
t <sub>ON</sub>	Turn On Time	V <sub>CC</sub> = 125V, I <sub>C</sub> = 1A			1.1	μs
t <sub>STG</sub>	Storage Time	$I_{B1} = -I_{B2} = -0.2A$ $R_1 = 125\Omega$			4.0	μs
t <sub>F</sub>	Fall Time	11 - 12022			0.7	μs

# Thermal Characteristics $T_C = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Rating	Units
$R_{\theta JC}$	Thermal Resistance Junction-Case	48	°C/W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient	125	°C/W

### **Typical Performance Characteristics**

Figure 1. Static Characteristic

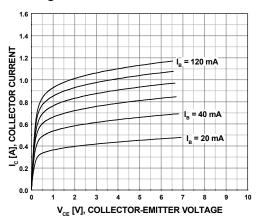


Figure 2. DC Current Gain

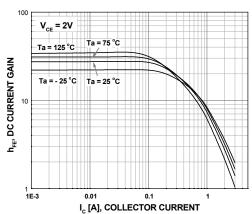


Figure 3. Collector-Emitter Saturation Voltage

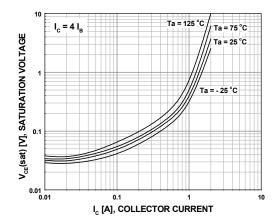


Figure 4. Base-Emitter Saturation Voltage

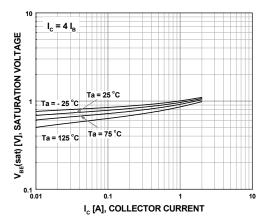


Figure 5. Resistive Load Switching Time

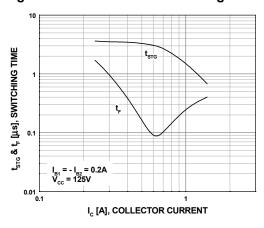
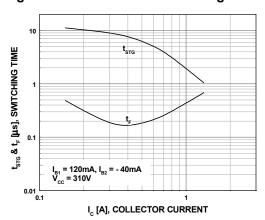


Figure 6. Resistive Load Switching Time



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## Typical Performance Characteristics (Continued)

Figure 7. Forward Biased Safe Operating Area

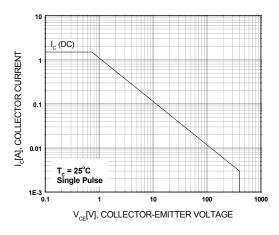


Figure 8. Reverse Biased Safe Operating Area

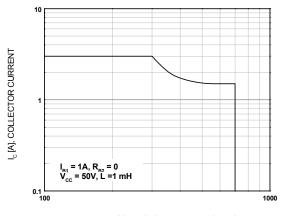
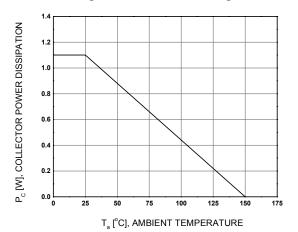


Figure 9. Power Derating

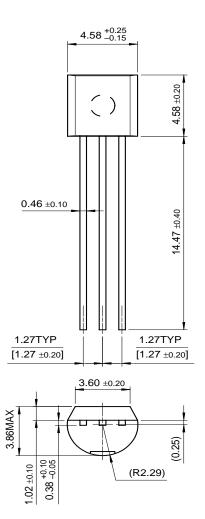


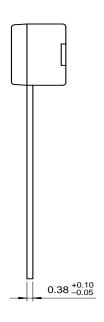
 $V_{\text{CE}}$  [V], COLLECTOR-EMITTER VOLTAGE

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### **Mechanical Dimensions**

TO-92





Dimensions in Millimeters

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Rev. I15





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### **FJN3303**

NPN Silicon Transistor Planar Silicon Transistor

#### **Contents**

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#### **Features**

- High Voltage Capability
- High Switching Speed
- Suitable for Electronic Ballast and Charger

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Product status/pricing/packaging

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Product	Product status	Pb-free Status	Pricing*	Package type	Leads	Packing method	Package Marking Convention**
FJN3303BU	Full Production	Full Production	\$0.104	<u>TO-92</u>	3	BULK	<u>Line 1:</u> R3305
FJN3303TA	Full Production	Full Production	\$0.104	<u>TO-92</u>	3	AMMO	<u>Line 1:</u> R3305

<sup>\*</sup> Fairchild 1,000 piece Budgetary Pricing

Indicates product with Pb-free second-level interconnect. For more information click here.

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Product
<u>FJN3303BU</u>
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